Erratum

Correction to A Finite-Field Approach for *GW* Calculations beyond the Random Phase Approximation

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 I_{GW} n ref 1, a coding error led to inaccuracies in the calculation of GW quasiparticle (QP) energies evaluated beyond the random phase approximation (RPA). After correcting the



Figure 5. Difference (ΔE) between vertical ionization potential (VIP) and vertical electron affinity (VEA) of molecules in the GW100 set computed at the $G_0 W_0^{f_w}/G_0 W_0 \Gamma_0$ level and corresponding $G_0 W_0^{RPA}$ results. Mean deviations (MDs) in electronvolts are shown in brackets and represented with black dashed lines. Results are presented for three different functionals (LDA, PBE, and PBE0) in the top, middle, and bottom panel, respectively.

implementation, the conclusions of our original contribution remain valid.

Here we report updated Figures 5-7 and Tables 1 and 2. The major difference between the updated results and the original ones was found for the quasiparticle (QP) energies of molecules computed at the $G_0 W_0^{f_{xx}}$ level. In Figure 5 we show the mean deviation (MD) of $G_0 W_0^{f_{\rm ac}}$ and $G_0 W_0 \Gamma_0$ results from $G_0 W_0^{\rm RPA}$ results. The MD between $G_0 W_0^{f_{xx}}$ and $G_0 W_0^{RPA}$ is -0.15/-0.13/-0.24 eV for the vertical ionization potential (VIP) and 0.15/0.15/0.23 eV for the vertical electron affinity (VEA) with the LDA/PBE/DDH functional, respectively (in ref 1. the MD was 0.30/0.31/0.58 eV for VIP and -0.01/-0.01/0.01 eV for VEA). Although the updated MD values are different from those of ref 1, this difference does not affect our original conclusions, i.e., that the effect of vertex correction at the $G_0 W_0^{f_{\rm NC}}$ level is less significant than that found at the $G_0 W_0 \Gamma_0$ level. We found that the MD between $G_0 W_0 \Gamma_0$ and $G_0 W_0^{\text{RPA}}$ results is -0.35/-0.56/-0.40 eV for VIP and -0.49/-0.59/-0.66 eV for VEA with the LDA/PBE/DDH functional, respectively (in ref 1. the MD was -0.74/-0.76/-1.25 eV for VIP and -0.26/-0.30/-0.32 eV). The trend that both VIP and VEA obtained at the $G_0 W_0 \Gamma_0$ level are lower than those obtained at the $G_0 W_0^{\text{RPA}}$ level is the same as that reported in ref 1.

For solids, the updated band gap values (Table 2) are similar to those in ref 1, with the mean absolute deviation (MAD) between current and previous results being 0.17 eV for $G_0 W_0^{f_{xx}}$ calculations (fifth column) and 0.06 eV for $G_0 W_0 \Gamma_0$ calculations (sixth column). The largest difference was found in the case of $G_0 W_0^{f_{xx}}$ calculations of WO₃ and Si₃N₄, where the updated results are ~0.3 eV lower than previous ones. The conclusion that in solids the effect of vertex corrections is much smaller than in molecules remains the same.

We emphasize that while the specific numbers reported in the updated tables and figures are different from the corresponding ones in ref 1, the trends observed here are the same as those reported previously and therefore the major conclusions of ref 1

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Figure 6. Vertical ionization potential (VIP), vertical electron affinity (VEA) and electronic gap of molecules in the GW100 set computed at $G_0 W_0^{\text{RPA}}$, $G_0 W_0^{f_{sc}}$, and $G_0 W_0 \Gamma_0$ levels of theory, compared to experimental and CCSD(T) results (black dashed lines).



Figure 7. *GW* quasiparticle corrections to the valence band maximum (VBM) and the conduction band minimum (CBM). Circles, squares, and triangles are $G_0 W_0^{\text{RPA}}$, $G_0 W_0^{f_{sc}}$, and $G_0 W_0 \Gamma_0$ results, respectively; red, blue, and green markers correspond to calculations with LDA, PBE, and DDH functionals.

Table 1. I	Mean Deviation an	d Mean Absolut	e Deviation (i	n Brackets)	for GW	Results	Compared to	Experimental	Results and
CCSD(T)	Calculations ^a						-	-	

	CCSD(T) VIP	exp VIP	exp VEA	exp gap
$G_0 W_0^{\text{RPA}}$ @LDA	-0.23 (0.34)	-0.19 (0.43)	0.04 (0.45)	0.21 (0.56)
$G_0 W_0^{f_{\mathrm{sc}}}$ @LDA	-0.39 (0.48)	-0.35 (0.53)	0.21 (0.51)	0.50 (0.69)
$G_0 W_0 \Gamma_0 $ @LDA	-0.58 (0.62)	-0.54 (0.63)	-0.49 (0.59)	0.04 (0.53)
$G_0 W_0^{\text{RPA}}$ @PBE	-0.43 (0.50)	-0.39 (0.55)	-0.09 (0.46)	0.28 (0.57)
$G_0 W_0^{f_{\mathrm{sc}}}$ @PBE	-0.56 (0.62)	-0.52(0.65)	0.08 (0.49)	0.56 (0.75)
$G_0 W_0 \Gamma_0 @PBE$	-0.99 (1.01)	-0.95 (0.98)	-0.77(0.84)	0.15 (0.58)
$G_0 W_0^{\text{RPA}}$ @PBE0	-0.05 (0.20)	-0.01 (0.34)	-0.26 (0.41)	-0.26 (0.47)
$G_0 W_0^{f_{\mathrm{sc}}}$ @PBE0	-0.29 (0.39)	-0.25(0.48)	0.04 (0.43)	0.26 (0.52)
$G_0 W_0 \Gamma_0 @PBE0$	-0.45 (0.49)	-0.41 (0.54)	-1.10 (1.11)	-0.68(0.75)

"We report vertical ionization potentials (VIP), vertical electron affinities (VEA), and the fundamental electronic gaps. All values are given in electronvolts.

remain unaltered. All of the equations in ref 1 remain unchanged.

Finally, we note that the update discussed here does not involve changes to the implementation of the finite-field Table 2. Band Gaps (eV) for Solids Computed by Different GW Approximations and Exchange-Correlation (XC) Functionals (See Text)^{*a*}

system	XC	DFT	$G_0 W_0^{\text{RPA}}$	$G_0 W_0^{f_{\mathrm{xc}}}$	$G_0 W_0 \Gamma_0$
Si	LDA	0.55	1.35	1.32	1.26
	PBE	0.73	1.39	1.36	1.31
	DDH	1.19	1.57	1.48	1.51
С	LDA	4.28	5.99	5.92	5.88
	PBE	4.46	6.05	5.97	5.93
SiC (4H)	LDA	2.03	3.27	3.16	3.24
	PBE	2.21	3.28	3.15	3.25
AlN	LDA	3.85	5.67	5.51	5.89
	PBE	4.04	5.67	5.48	5.83
WO ₃ (monoclinic)	LDA	1.68	3.10	2.69	3.26
	PBE	1.78	2.97	2.52	3.13
Si ₃ N ₄ (amorphous)	LDA	3.04	4.84	4.65	4.83
	PBE	3.19	4.87	4.64	4.84
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^{*a*}All calculations are performed at the Γ -point of supercells with 64–96 atoms (see section 1 of the Supporting Information for details).

algorithm presented in ref 1 for the calculation of response functions and exchange—correlation kernels. Therefore subsequent works of ref 1 that deploy the finite-field algorithm and its original implementation (e.g., ref 2) remain unaltered.

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